

In the Claims

Claims 1-14 (Canceled).

15. An apparatus comprising:
 - a semiconductor substrate having a barrier layer formed thereon;
 - a trench etched into the substrate adjacent the barrier layer;
 - a dielectric layer deposited over the barrier layer and trench; and
 - a plurality of ions implanted into the dielectric layer.
16. The apparatus of claim 14 further comprising a plurality of ions implanted into the barrier layer.
17. The apparatus of claim 14 wherein the barrier layer comprises a silicon nitride layer.
18. The apparatus of claim 14 wherein the dielectric layer comprises a silicon oxide layer.
19. The apparatus of claim 14 wherein the dielectric layer is damaged by the plurality of implanted ions.
20. The apparatus of claim 14 wherein the plurality of ions are selected from the group consisting of silicon, carbon, nitrogen, and oxygen.